

Amendments to the Specification

Please replace paragraph [0001] at page 1 of the specification with the following new paragraph [0001]:

[0001] This application is a continuation-in-part of U.S. Patent Application No. 10/379,466, filed 4 March 2003, now U.S. Patent No. 7,098,149, the disclosure of which is incorporated herein by reference in its entirety.

Please replace paragraph [0044] at page 12 of the specification with the following new paragraph [0044]:

[0044] In a certain preferred embodiment of the present invention wherein the organosilicate glass film consists essentially of Si, C, O, H, and optionally F, the film is formed by providing a substrate within a vacuum chamber; introducing into the vacuum chamber chemical reagents that comprise at least one structure-former precursor selected from the group consisting of an organosilane and an organosiloxane, and optionally a pore-former precursor distinct from the at least one structure-former precursor; and applying energy to the reagents in said chamber to induce reaction of the reagents and to form the film on the substrate. Examples of chemical reagents used as structure-former and pore-former precursors may be found in pending U. S. Patent Applications Attorney Docket Nos. 06063USA, 06274PUSA, 06150USA, and 06336PUSA Nos. 6,583,048, 6,846,515, and 6,716,770, and U.S. patent application Publication No. 2004/0096593 A1, which are commonly assigned to the assignee of the present invention and incorporated herein by reference in ~~its~~ their entirety.

Please replace paragraph [0055] at page 16 to page 17 of the specification with the following new paragraph [0055]:

[0055] In certain embodiments of the present invention, a single compound may function as both the structure-former and pore-former within the porous OSG film. That is, the structure-former precursor and the pore-former precursor are not necessarily different compounds, and in certain embodiments, the pore-former is a part of (e.g., covalently bound to) the structure-former precursor. Examples of these materials may be found, for example, in pending U. S. Patent Applications, Attorney Docket Nos. ~~06150~~USA 6,716,770 and ~~06274~~USA 6,846,515, that are commonly assigned to the assignee of the present invention and incorporated herein by reference in ~~its~~ their entirety. For example, it is possible to use 1-neohexyl-1,3,5,7-tetramethyl-cyclotetrasiloxane ("neohexyl TMCTS") as a single species, whereby the TMCTS portion of the molecule forms the base OSG structure and the bulky alkyl substituent neohexyl is the pore-former species which is removed, for example, during the anneal process. Having the pore-former attached to a Si species that will network into the OSG structure may be advantageous in achieving a higher efficiency of incorporation of pore-former into the film during the deposition process. Furthermore, it may also be advantageous to have two pore-formers attached to one Si in the precursor, such as in di-neohexyl-diethoxysilane, or two Si's attached to one pore-former, such as in 1,4-bis(diethoxysilyl)cyclohexane. While not intending to be bound by theory, the reaction of one Si-pore-former bond in the plasma may enable the the incorporation of the second pore-former group into the deposited film.

Please replace paragraph [0079] at page 23 to page 24 of the specification with the following new paragraph [0079]:

[0079] The present invention also discloses a mixture for forming a dense or a porous OSG film having a dielectric constant of 3.5 or below suitable for exposure to UV light. The OSG film may be formed by a variety of deposition processes including CVD-related and spin-on-glass processes. For dense OSG films, the mixture comprises at least one structure-former precursor and/or resultant OSG film that exhibits an absorbance in the 200 to 400 nm wavelength range. For porous OSG films, the mixture may comprise from 5% to 95% by weight of a structure-former precursor and from 5% to 95% by weight of a pore-former precursor wherein the at least one of the precursors and/or the organosilicate film exhibits an absorbance in the 200 to 400 nm wavelength range. Depending upon the deposition process, such as for spin-on-glass deposition, the mixture may comprise additional additives, for example, a solvent, a catalyst, a surfactant, water, and the like. Additional additives to the mixture used for spin-on-glass deposition may be found, for example, in pending U. S. ~~Patent Applications Attorney Docket No. 06336PUSA~~ patent application Publication No. 2004/0096593 A1, which is commonly assigned to the assignee of the present invention and incorporated herein by reference in its entirety.